

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	15	silicon with seed and polysilic\$3 with (thin near transistor tft) and evaporation	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 12:54
S2	1	10/604883	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/02/23 15:21
S3	0	("2004/0247786").URPN.	USPAT	OR	ON	2006/02/23 15:21
S4	7	((mao\$1yi chih\$1chin) near chang).in. (wung near chien\$1shen).in.	USPAT	OR	ON	2006/02/23 15:22
S5	27	((mao\$1yi chih\$1chin) near chang).in. (wung near chien\$1shen).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/02/23 15:23
S6	27	((mao\$1yi chih\$1chin) near chang).in. (wung near chien\$1shen).in. and silicon near seed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/02/23 15:41
S7	690	438/48\$.ccls. and evaporation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/02/23 15:43
S8	2	438/48\$.ccls. and (oblique angle\$5) near3 evaporation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 12:11
S9	0	438/48\$.ccls. and silicon near seed same evaporation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/02/23 15:52
S10	2	"4860939".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/02/23 15:52
S11	18	427/497,248.1,250,255.7,259,272,282.ccls. and oblique near evaporat\$5	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 12:56

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S12	4	427/497,248.1,250,255.7,259,272,282.ccls. and evaporat\$5 and silicon near seed	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 12:57
S13	15	"427"/\$.ccls. and evaporat\$5 and silicon near seed	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 12:58
S14	1	"427"/\$.ccls. and silicon near seed and oblique	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 12:58
S15	18	"427"/\$.ccls. and evaporat\$5 and silicon and polysilicon and oblique	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:16
S16	8	("4599135" "4756810" "4792842" "4874493" "5420072" "5725739" "5730835" "5985103").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/03/06 13:02
S17	5	("6106677").URPN.	USPAT	OR	ON	2006/03/06 13:12
S18	1	"427"/\$.ccls. and evaporat\$5 and silicon with seed and oblique	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:18
S19	42	evaporat\$5 and silicon with seed and oblique	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:20
S20	0	("2004/0247786").URPN.	USPAT	OR	ON	2006/03/06 13:20
S21	257	evaporat\$5 and silicon with seed and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:26
S22	249	evaporat\$5 and seed with crystal and polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:26
S23	43	evaporat\$5 and seed with crystal same polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:27
S25	6	oblique near evaporat\$5 and silicon near3 (seed crystal) same polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:31

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S27	57	evaporat\$5 same silicon near3 (seed crystal) same polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:31.
S29	38	"427"/\$.ccls. and evaporat\$5 and silicon near3 (seed crystal) same polysilicon	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:36
S30	18	"427"/\$.ccls. and evaporat\$5 and silicon near3 (seed crystal) same polysilicon and (angle oblique angul\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:41.
S32	326	evaporat\$5 and silicon near3 (seed crystal) same polysilicon and (angle oblique angul\$5)	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:53
S33	2	evaporat\$5 and silicon near3 (seed crystal) same polysilicon and 427/551,552,596.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 13:53.
S34	2	evaporat\$5 and silicon near3 (seed crystal) same polysilic\$3 and 427/551,552,596.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 15:25
S35	1	evaporat\$5 and silicon near3 (seed crystal) same polysilic\$3 and 427/97.1,97.3,97.4,97.6.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 15:26.
S36	5	evaporat\$5 and silicon near3 (seed crystal) and 427/97.1,97.3, 97.4,97.6.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 15:28
S39	170	evaporat\$5 and (seed with crystal) and "427"/\$.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 15:28.
S40	23	evaporat\$5 and (seed with crystal) and "427"/\$.ccls. and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 15:33
S41	379	silicon near3 (seed crystal) and "427"/\$.ccls. and transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT	OR	ON	2006/03/06 15:33.

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S42	11	("4717462" "4724060" "4824544" "4834856" "4874493" "4983547" "5114556" "5302266" "5482611" "5486492" "5525543").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2006/03/06 15:47
S43	33	("5725739").URPN.	USPAT	OR	ON	2006/03/06 15:48
S44	24	("4256816").URPN.	USPAT	OR	ON	2006/03/06 16:12
S45	19	S44 and silicon	USPAT	OR	ON	2006/03/06 16:12
S48	24	("4256816").URPN.	USPAT	OR	ON	2006/03/06 16:37
S50	182	crystal near3 seed with control\$4 and mask\$6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/06 16:39
S51	124	crystal near3 seed with control\$4 and mask\$6 and silic\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/06 16:48
S52	7	("5447117").URPN.	USPAT	OR	ON	2006/03/06 16:48
S53	16	crystal near3 seed with control\$4 and mask\$6 and silic\$5 and oblique	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/06 17:07
S54	2	"5447117".pn.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/06 17:07
S55	7	("5447117").URPN.	USPAT	OR	ON	2006/03/06 17:07
S56	4	crystal near3 seed and mask\$6 and oblique with evaporation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/06 17:09
S57	20	crystal near3 seed and oblique with evaporation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/06 17:10
S58	2	crystal near3 seed and patterning and oblique with evaporation	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/06 17:10

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S59	90	crystal near3 seed and patterning and oblique	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:14
S60	211	crystal with seed and oblique and mask\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:15
S61	4	crystal with seed and oblique with evaporation and mask\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:15
S62	1	crystal with seed and oblique with evaporation and shield\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:16
S63	197	crystal with seed and oblique and mask\$3 and (silic\$3 si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:40
S64	0	crystal with seed and oblique and lift\$4off near mask\$3 and (silic\$3 si)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:40
S65	0	crystal with seed and oblique and lift\$4off near mask\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:40
S66	869	lift\$4off near mask\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:40
S67	112	lift\$4off near mask\$3 and seed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:42
S68	5	lift\$4off near mask\$3 and crystal with seed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:41

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S69	92	lift\$4off near mask\$3 and seed near layer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:47
S70	46	lift\$4off near mask\$3 and seed near layer and (oblique angl\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:47
S71	46	lift\$4off near mask\$3 and seed near layer and (oblique angl\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:48
S72	54	lift\$4off near mask\$3 and seed and (oblique angl\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:48
S73	8	S72 not S71	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 10:56
S74	317	"427"/\$.ccls. and seed near layer and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:50
S75	2	oblique near evaporation and seed near layer and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:03
S76	2	oblique near evaporat\$5 and seed near layer and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:01
S77	7	angl\$4 near evaporat\$5 and seed near layer and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:03
S78	12	angl\$4 with evaporat\$5 and seed near layer and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:03

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S79	8	oblique near deposition and seed near layer and mask\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:04
S80	3	(LTPS low near temperature near polysilic\$3) and oblique near (evaporat\$4 deposit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:30
S81	355	(LTPS low near temperature near polysilic\$3 TFT thin near4 transistor) and oblique near (evaporat\$4 deposit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:36
S82	18	(LTPS low near temperature near polysilic\$3 TFT thin near4 transistor) and oblique near (evaporat\$4 deposit\$4) and seed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:37
S83	47	427/259,269-272.ccls. and seed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:53
S84	29	427/259,269-272.ccls. and oblique	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:58
S85	0	427/259,269-272.ccls. and silic\$3 near seed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 11:57
S86	39	427/282.ccls. and oblique	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 12:08
S87	48	427/282.ccls. and seed	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 12:09
S88	26	438/48\$.ccls. and (oblique) and seed and mask\$5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	ON	2006/03/07 12:11